

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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Docket Number (Optional) <b>100-22900 (P05685)</b>		Application Number <b>New</b>	
Applicant(s) <b>Vladislav Vashchenko et al.</b>			
Filing Date <b>Herewith</b>		Group Art Unit <b>Unknown</b>	

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>W</i>		Pat. Appln. 10/649,989		Vladislav Vashchenko et al.			08/27/03
<i>W</i>		Pat. Appln. 10/650,000		Vladislav Vashchenko et al.			08/27/03
<i>W</i>		6,433,368 B1	08/13/02	Vladislav Vashchenko et al.	257	173	01/22/01

## FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>W</i>		G. Charitat, "Voltage Handling Capability and Termination Techniques of Silicon Power Semiconductor Devices", IEEE BCTM 11.1, 2001, pps. 175-183.
<i>W</i>		Julian Z. Chen, Ajith Amerasekera and Tom Vrotsos, "Bipolar SCR ESD Protection Circuit for High Speed Submicron Bipolar/BiCMOS Circuits", IEDM, pps. 337-340, (14.1 - 14.1.4), 1995, IEEE.

EXAMINER <i>Kevin Quah</i>	DATE CONSIDERED <i>5/17/04</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.